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# PSMN4R0-30YLD

N-channel 30 V, 4.0 mΩ logic level MOSFET in LPAK56  
using NextPowerS3 Technology

10 October 2013

Product data sheet

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LPAK56 package. NextPowerS3 portfolio utilising NXP's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

## 2. Features and benefits

- Ultra low  $Q_G$ ,  $Q_{GD}$  and  $Q_{OSS}$  for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

## 3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ $T_j$ ≤ 175 °C	-	-	30	V
$I_D$	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; <a href="#">Fig. 1</a>	-	-	95	A
$P_{tot}$	total power dissipation	$T_{mb}$ = 25 °C; <a href="#">Fig. 2</a>	-	-	64	W



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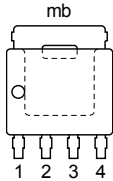
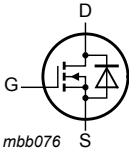
## PSMN4R0-30YLD

N-channel 30 V, 4.0 mΩ logic level MOSFET in LPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	4.4	5.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	3.4	4	mΩ
Dynamic characteristics							
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	2.4	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	9.1	-	nC
Source-drain diode							
S	softness factor	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; dI <sub>S</sub> /dt = -100 A/μs; V <sub>DS</sub> = 15 V; <a href="#">Fig. 16</a>		-	1.1	-	

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p><b>LPAK56; Power-SO8 (SOT669)</b></p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R0-30YLD	LPAK56; Power-SO8	Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R0-30YLD	4D030L

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## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

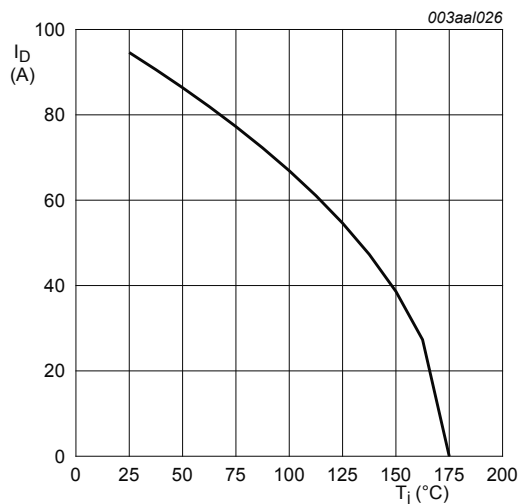
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		-	30	V
$V_{DGR}$	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>		-	95	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 1</a>		-	67	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a>		-	378	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>		-	64	W
$T_{stg}$	storage temperature			-55	175	°C
$T_j$	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
$V_{ESD}$	electrostatic discharge voltage	HBM		375	-	V
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$		-	54	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$		-	378	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(\text{init})} = 25\text{ °C}$ ; $I_D = 25\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; unclamped; $t_p = 129\text{ }\mu\text{s}$	<a href="#">[1]</a>	-	63	mJ

[1] Protected by 100% test

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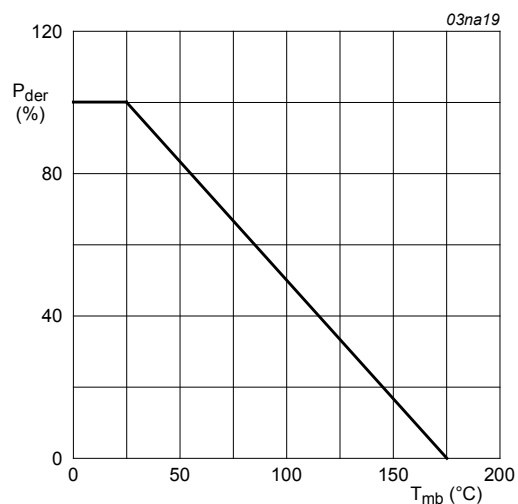
## PSMN4R0-30YLD

N-channel 30 V, 4.0 mΩ logic level MOSFET in LPAK56 using  
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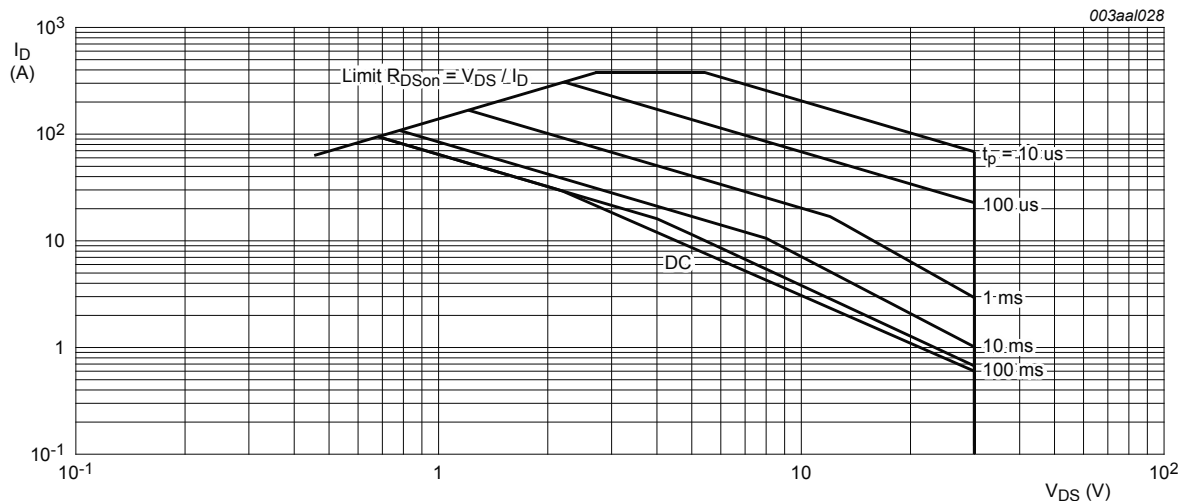
**Fig. 1.** Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$



**Fig. 2.** Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



**Fig. 3.** Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25^{\circ}C; I_{DM} \text{ is a single pulse}$$

## 9. Thermal characteristics

**Table 6.** Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6	-	2.14	2.33	K/W

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 4	-	50	-	K/W
		Fig. 5	-	125	-	K/W

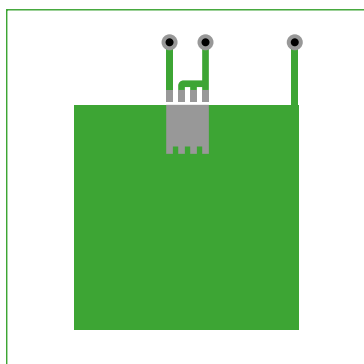


Fig. 4. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

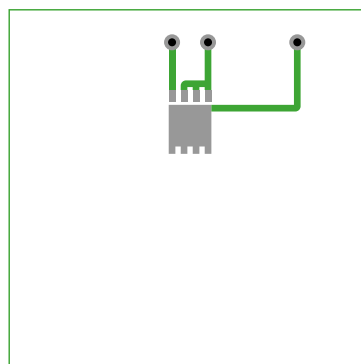


Fig. 5. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

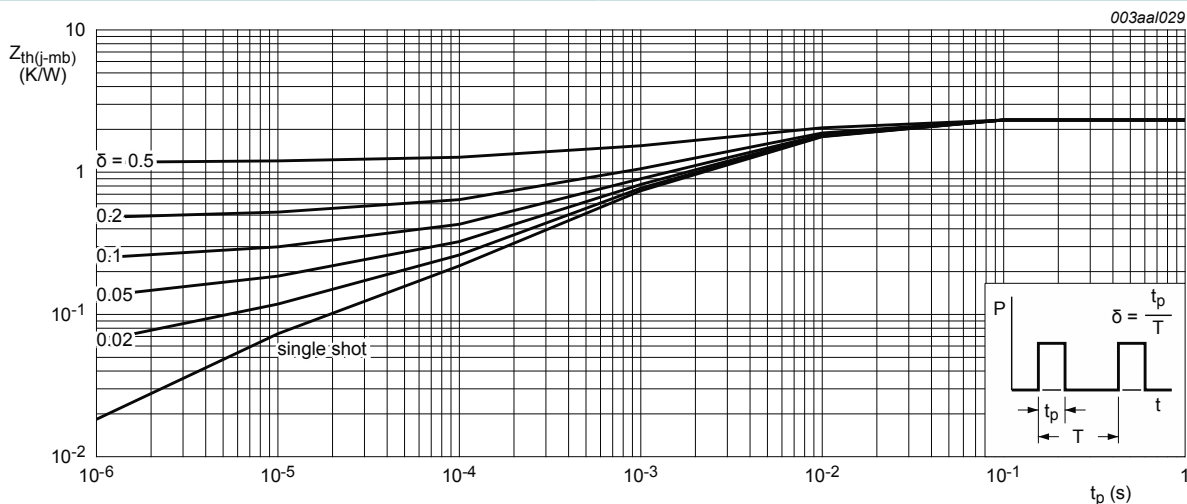


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_J = 25^\circ C$	30	-	-	V
		$I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_J = -55^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA$ ; $V_{DS} = V_{GS}$ ; $T_J = 25^\circ C$	1.2	1.74	2.2	V

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25\text{ }^{\circ}\text{C} < T_j < 150\text{ }^{\circ}\text{C}$	-	-4.1	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 24\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	1	μA
		$V_{DS} = 24\text{ V}; V_{GS} = 0\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	100	μA
$I_{GSS}$	gate leakage current	$V_{GS} = 16\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
		$V_{GS} = -16\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^{\circ}\text{C};$ <a href="#">Fig. 10</a>	-	4.4	5.5	mΩ
		$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 150\text{ }^{\circ}\text{C};$ <a href="#">Fig. 11; Fig. 10</a>	-	-	9.1	mΩ
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^{\circ}\text{C};$ <a href="#">Fig. 10</a>	-	3.4	4	mΩ
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 150\text{ }^{\circ}\text{C};$ <a href="#">Fig. 11; Fig. 10</a>	-	-	6.6	mΩ
$R_G$	gate resistance	$f = 1\text{ MHz}$	-	2.2	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 10\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	19.4	-	nC
		$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 4.5\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	9.1	-	nC
		$I_D = 0\text{ A}; V_{DS} = 0\text{ V}; V_{GS} = 10\text{ V}$	-	18.2	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 4.5\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	2.6	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1.9	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.7	-	nC
$Q_{GD}$	gate-drain charge		-	2.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\text{ A}; V_{DS} = 15\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	2.3	-	V
$C_{iss}$	input capacitance	$V_{DS} = 15\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^{\circ}\text{C};$ <a href="#">Fig. 14</a>	-	1272	-	pF
$C_{oss}$	output capacitance		-	812	-	pF
$C_{rss}$	reverse transfer capacitance		-	87	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; R_L = 0.6\text{ }^{\circ}\Omega; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 5\text{ }^{\circ}\Omega$	-	10.7	-	ns
$t_r$	rise time		-	21.2	-	ns
$t_{d(off)}$	turn-off delay time		-	14.9	-	ns
$t_f$	fall time		-	11.7	-	ns

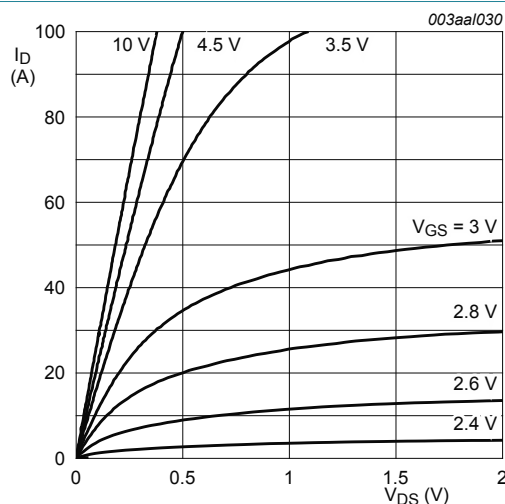
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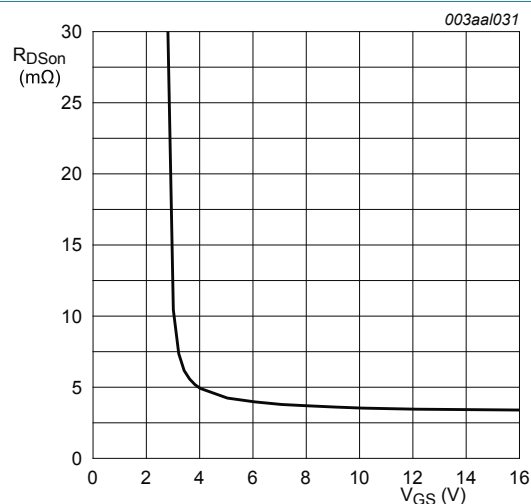
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{oss}$	output charge	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 15\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_j = 25\text{ °C}$	-	16	-	nC
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 15\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 15</a>	-	0.82	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A/}\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 15\text{ V}$ ; <a href="#">Fig. 16</a>	-	25.1	-	ns
$Q_r$	recovered charge		[1]	13.3	-	nC
$t_a$	reverse recovery rise time		-	11.9	-	ns
$t_b$	reverse recovery fall time		-	13.1	-	ns
S	softness factor		-	1.1	-	

[1] includes capacitive recovery



**Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values**

$T_j = 25\text{ °C}$



**Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values**

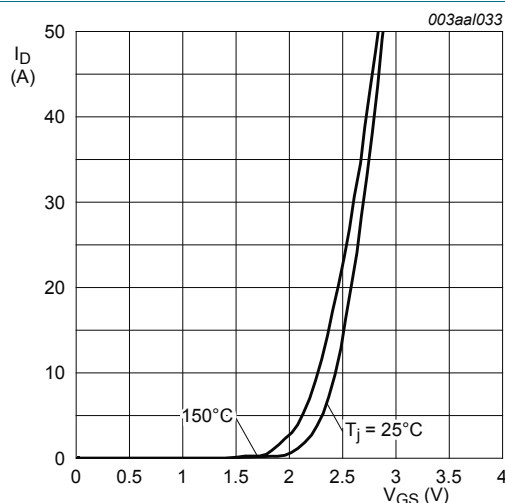
$T_j = 25\text{ °C}$ ;  $I_D = 25\text{ A}$



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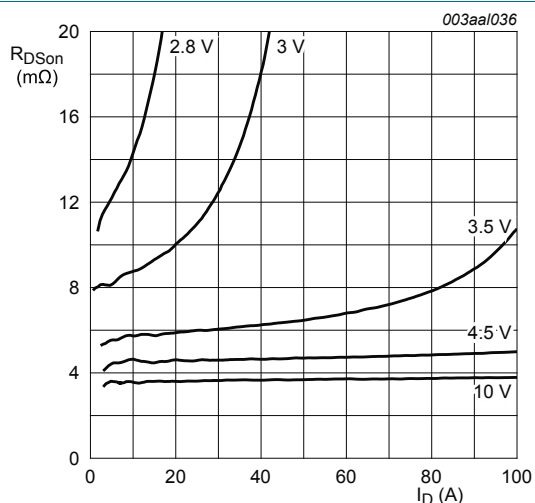
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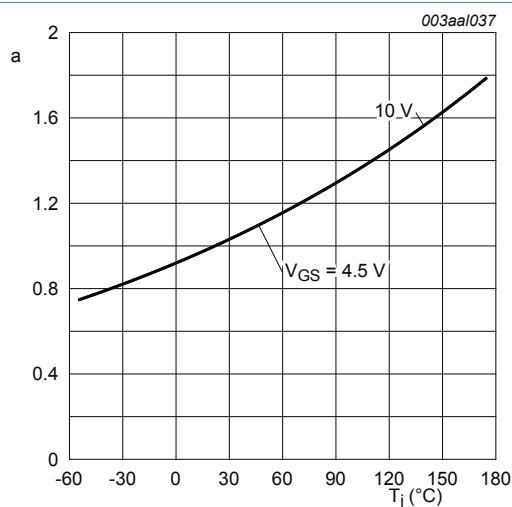
**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

$$V_{DS} = 12V$$



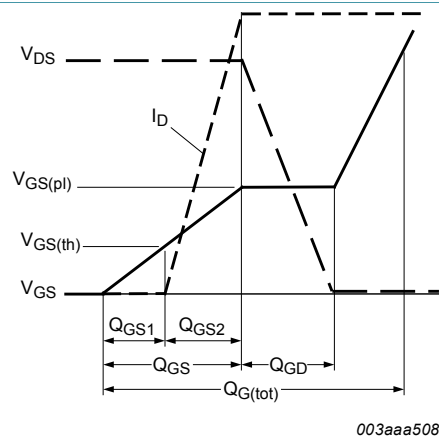
**Fig. 10. Drain-source on-state resistance as a function of drain current; typical values**

$$T_j = 25^\circ C$$



**Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ C)}$$

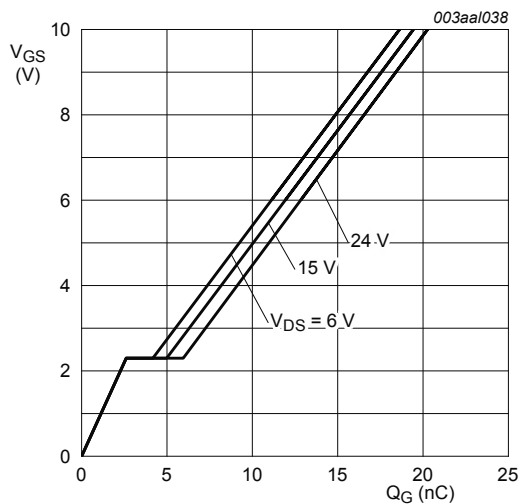


**Fig. 12. Gate charge waveform definitions**

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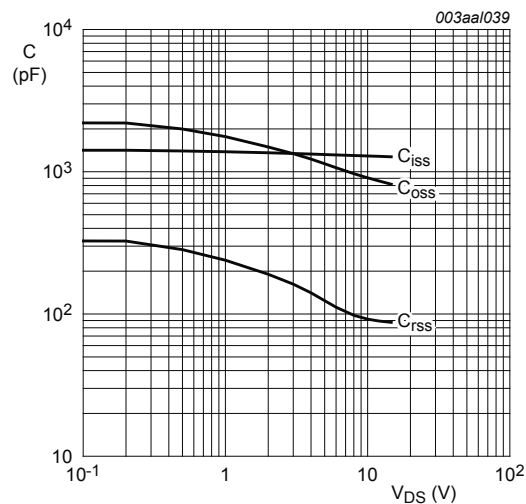
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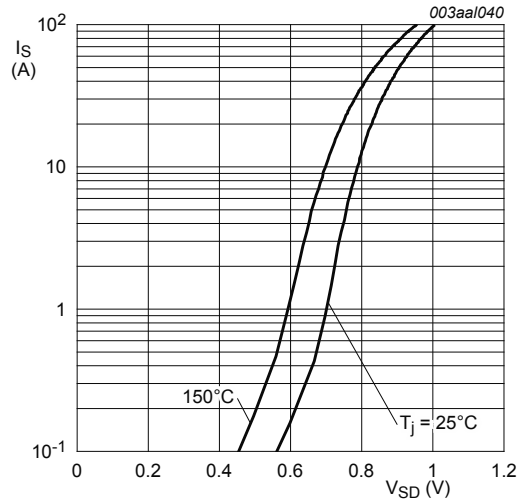
**Fig. 13. Gate-source voltage as a function of gate charge; typical values**

$T_j = 25^\circ\text{C}; I_D = 25\text{A}$



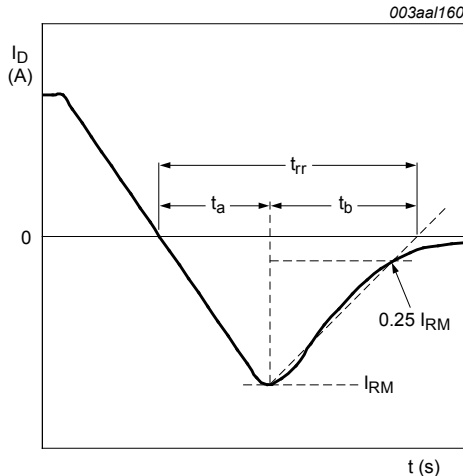
**Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$V_{GS} = 0\text{V}; f = 1\text{MHz}$



**Fig. 15. Source current as a function of source-drain voltage; typical values**

$V_{GS} = 0\text{V}$



**Fig. 16. Reverse recovery timing definition**

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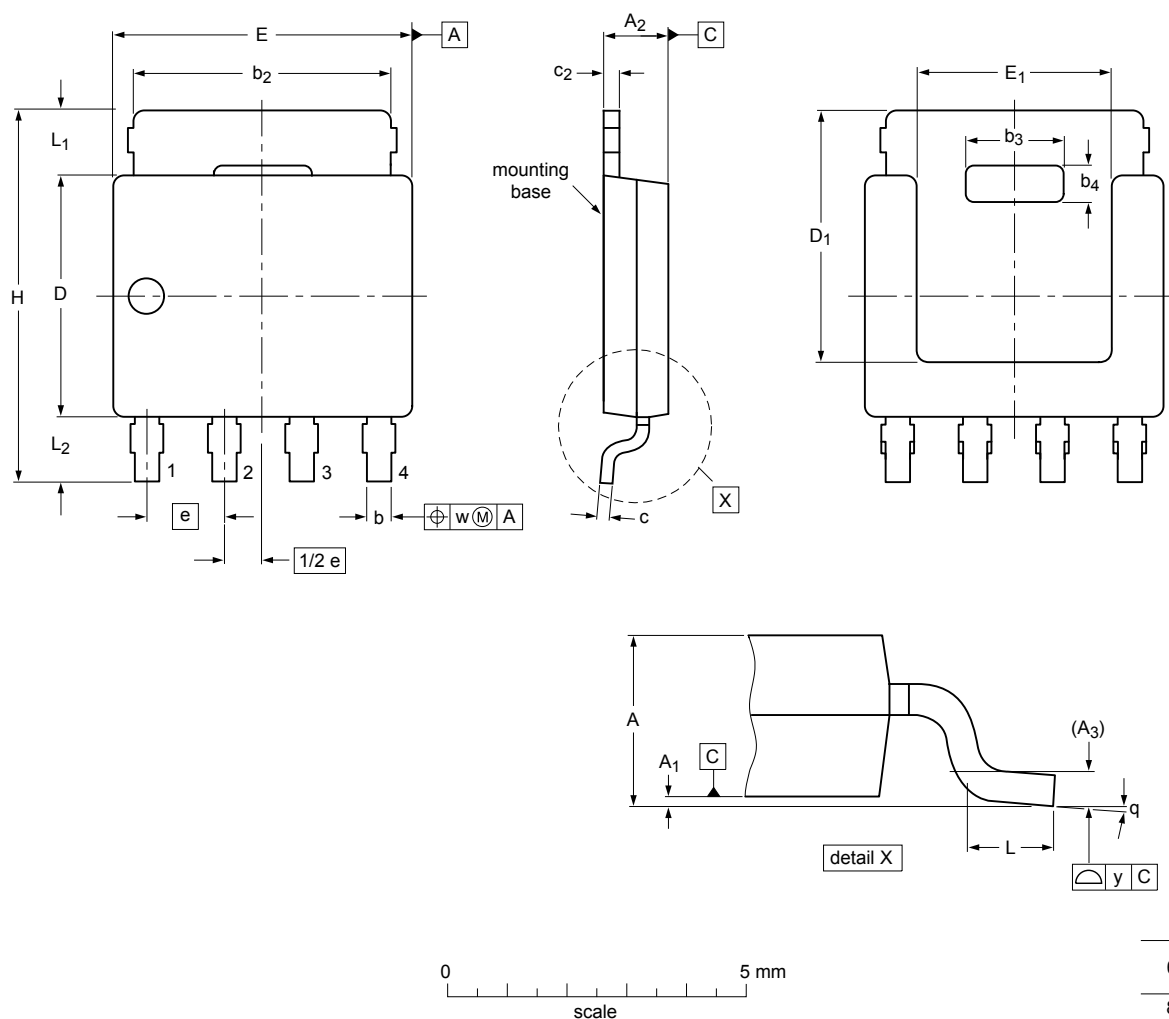
## PSMN4R0-30YLD

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### 11. Package outline

Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads

SOT669



Dimensions (mm are the original dimensions)

Unit <sup>(1)</sup>	A	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b	b <sub>2</sub>	b <sub>3</sub>	b <sub>4</sub>	c	c <sub>2</sub>	D <sup>(1)</sup>	D <sub>1</sub> <sup>(1)</sup>	E <sup>(1)</sup>	E <sub>1</sub> <sup>(1)</sup>	e	H	L	L <sub>1</sub>	L <sub>2</sub>	w	y
max	1.20	0.15	1.10		0.50	4.41	2.2	0.9	0.25	0.30	4.10	4.20	5.0	3.3	1.27	6.2	0.85	1.3	1.3	0.25	0.1
nom				0.25																	
min	1.01	0.00	0.95		0.35	3.62	2.0	0.7	0.19	0.24	3.80		4.8	3.1		5.8	0.40	0.8	0.8		

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

sot669\_po


Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT669		MO-235				-11-03-25- 13-02-27

Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

## NXP Semiconductors

## PSMN4R0-30YLD

### N-channel 30 V, 4.0 mΩ logic level MOSFET in LPAK56 using NextPowerS3 Technology

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 10 October 2013